

Automotive MOSFET

OptiMOS™-5 Power-Transistor



Features

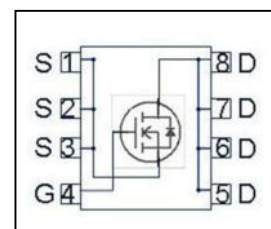
- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Logic Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

Potential applications

General automotive applications.

Product validation

Qualified for automotive applications. Product validation according to AEC-Q101.



Product Summary

V_{DS}	60	V
$R_{DS(on)}$	1.50	mΩ
I_D (chip limited)	230	A

Type	Package	Marking
IAUC120N06S5N015	PG-TDSON-8-43	5N06N015



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Maximum ratings

at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, Chip limitation ^{1,2)}	230	A
		$V_{GS}=10\text{ V}$, DC current ³⁾	120	
		$T_a=85\text{ °C}$, $V_{GS}=10\text{ V}$, R_{thJA} on 2s2p ^{2,4)}	30	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$, $t_p=100\text{ }\mu\text{s}$	757	
Avalanche energy, single pulse ²⁾	E_{AS}	$I_D=60\text{ A}$	345	mJ
Avalanche current, single pulse	I_{AS}	–	120	A
Gate source voltage	V_{GS}	–	± 20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	167	W
Operating and storage temperature	T_j, T_{stg}	–	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1	–	–	55/175/56	

Thermal characteristics²⁾

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	—	—	—	0.90	K/W
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	—	—	23.3	—	

Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$	60	—	—	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=94\text{ }\mu\text{A}$	2.2	2.8	3.4	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	—	—	1	μA
		$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}^{2)}$	—	—	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	—	—	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=7\text{ V}$, $I_D=30\text{ A}$	—	1.60	1.90	m Ω
		$V_{GS}=10\text{ V}$, $I_D=60\text{ A}$	—	1.30	1.50	
Gate resistance ²⁾	R_G	—	—	1.6	—	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics ²⁾						
Input capacitance	C _{iss}	V _{GS} =0 V, V _{DS} =30 V, f=1 MHz	–	5348	6952	pF
Output capacitance	C _{oss}		–	1160	1507	
Reverse transfer capacitance	C _{rss}		–	56	84	
Turn-on delay time	t _{d(on)}	V _{DD} =30 V, V _{GS} =10 V, I _D =60 A, R _{G,ext} =3.5 Ω	–	13	–	ns
Rise time	t _r		–	7	–	
Turn-off delay time	t _{d(off)}		–	27	–	
Fall time	t _f		–	17	–	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=30\text{ V}, I_D=60\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	–	24	31	nC
Gate to drain charge	Q_{gd}		–	13.7	21	
Gate charge total	Q_g		–	73.7	96	
Gate plateau voltage	$V_{plateau}$		–	4.5	–	V

Reverse Diode

Diode continuous forward current ²⁾	I_S	$T_C=25\text{ °C}$	–	–	120	A
Diode pulse current ²⁾	$I_{S,pulse}$	$T_C=25\text{ °C}, t_p=100\ \mu\text{s}$	–	–	757	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=60\text{ A}, T_j=25\text{ °C}$	–	0.8	1.1	V
Reverse recovery time ²⁾	t_{rr}	$V_R=30\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$	–	49	–	ns
Reverse recovery charge ²⁾	Q_{rr}		–	49	–	nC

¹⁾ Practically the current is limited by the overall system design including the customer-specific PCB.

²⁾ The parameter is not subject to production testing – specified by design.

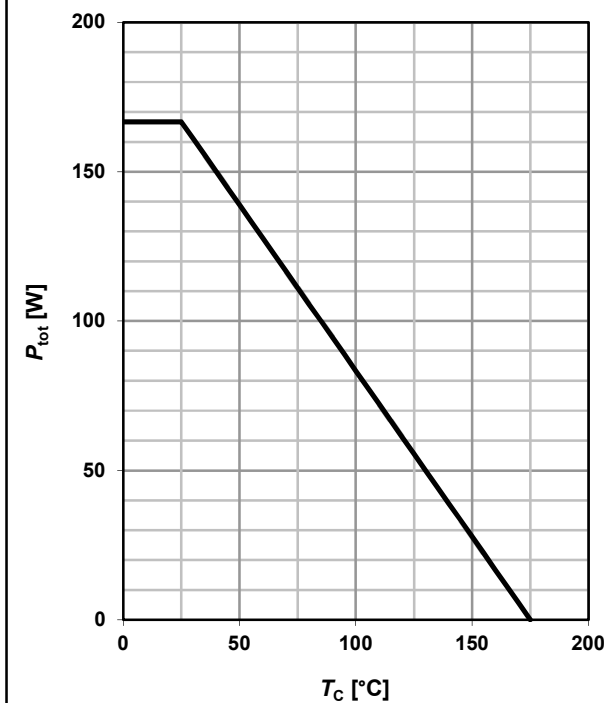
³⁾ Current is limited by package.

⁴⁾ Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

Electrical characteristics diagrams

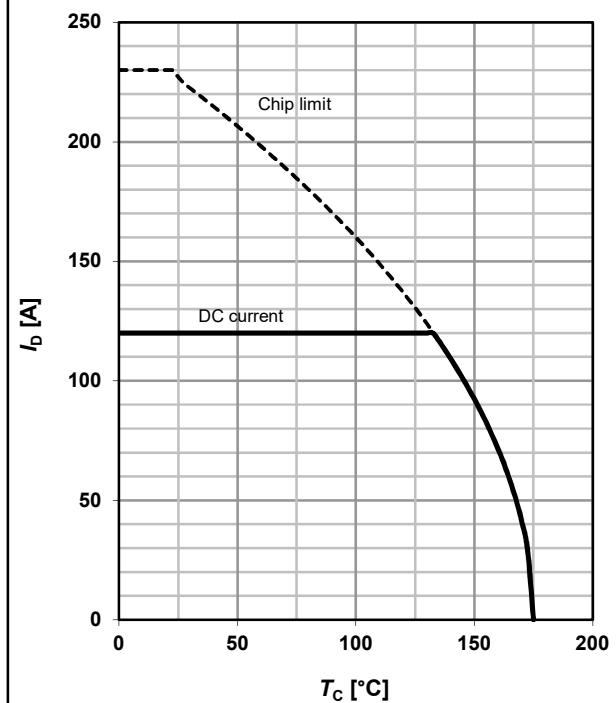
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} = 10 \text{ V}$$



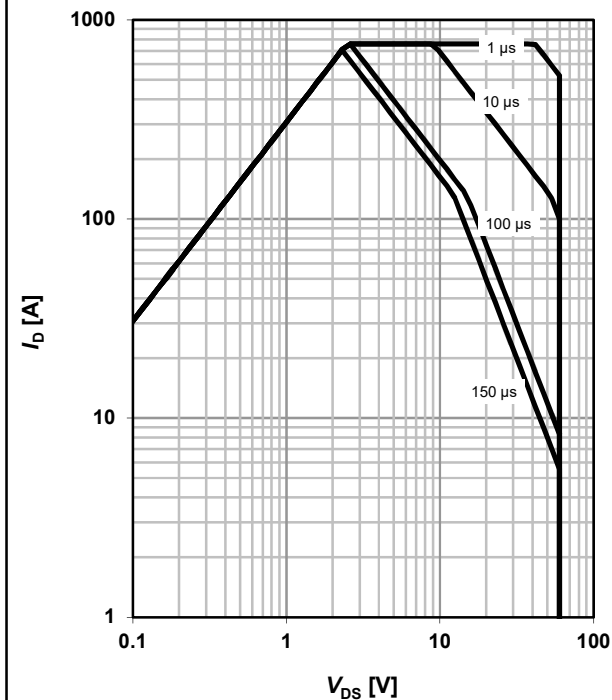
2 Drain current

$$I_D = f(T_C); V_{\text{GS}} = 10 \text{ V}$$



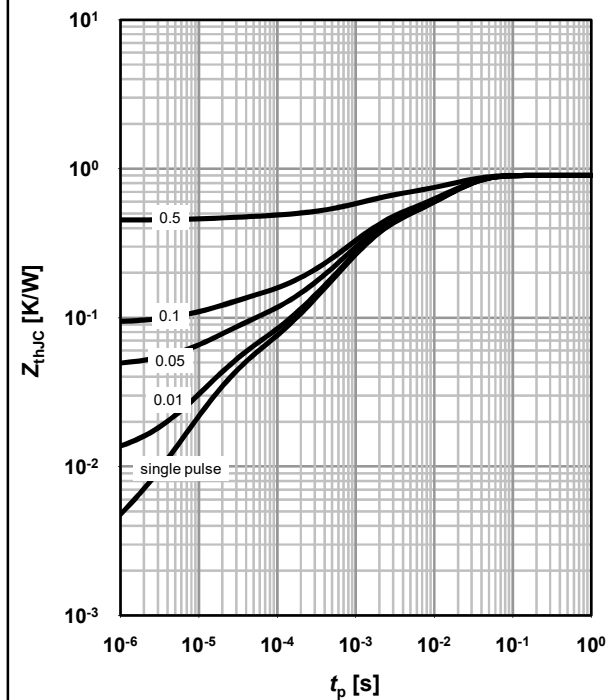
3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25^\circ\text{C}; D = 0; \text{parameter: } t_p$$



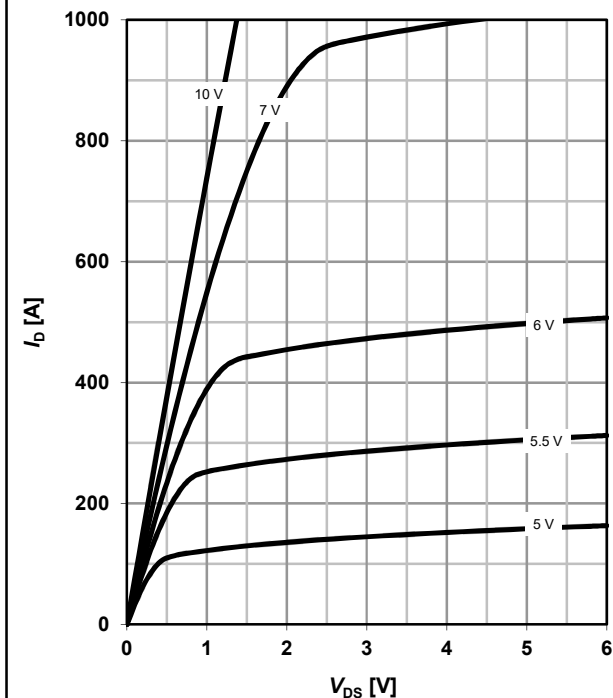
4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p); \text{parameter: } D = t_p/T$$



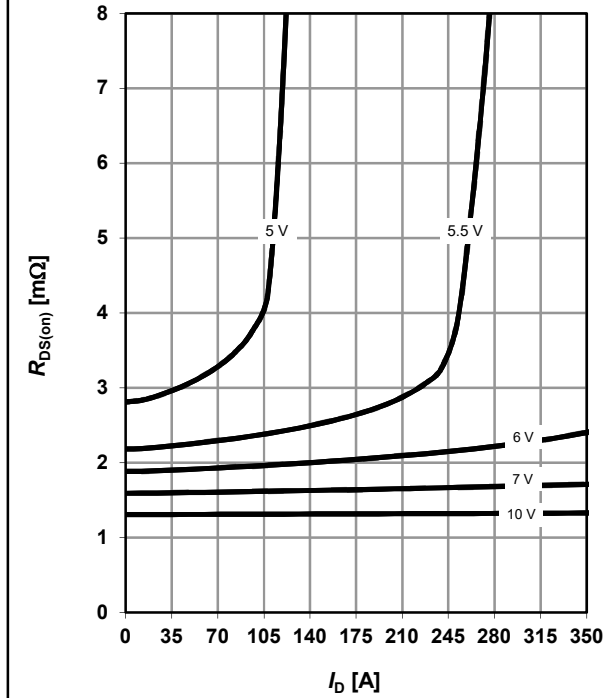
5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$



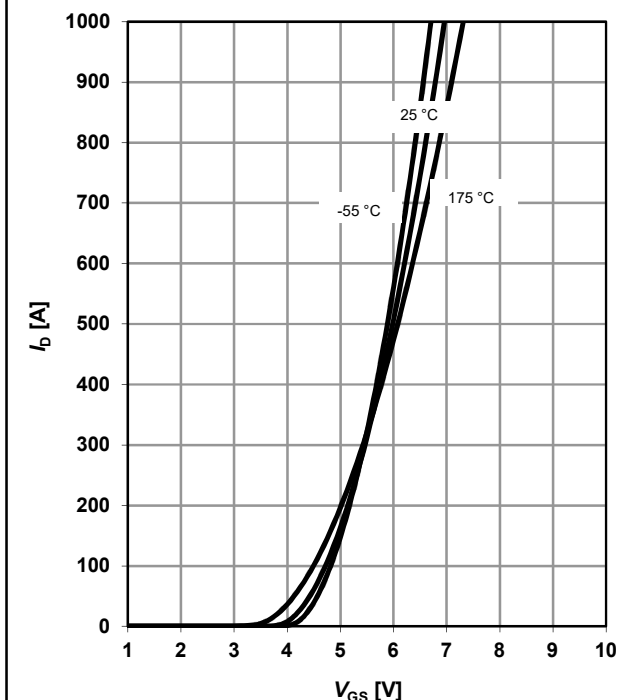
6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$



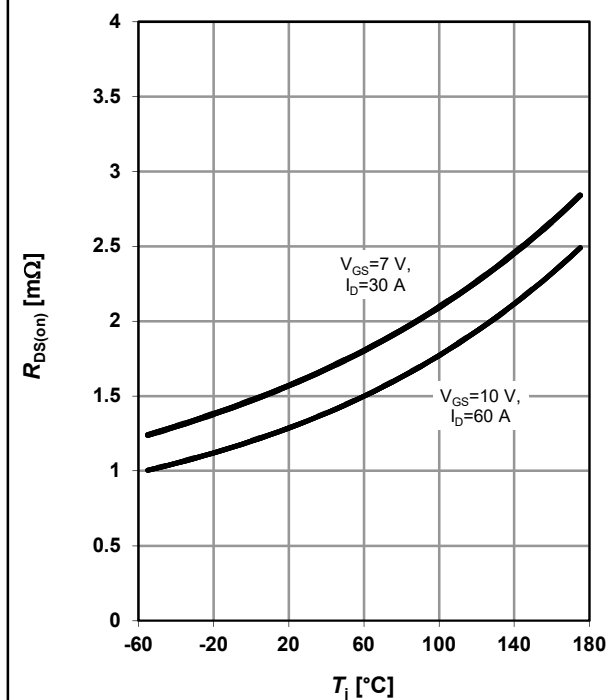
7 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} = 6\text{V}; \text{parameter: } T_j$

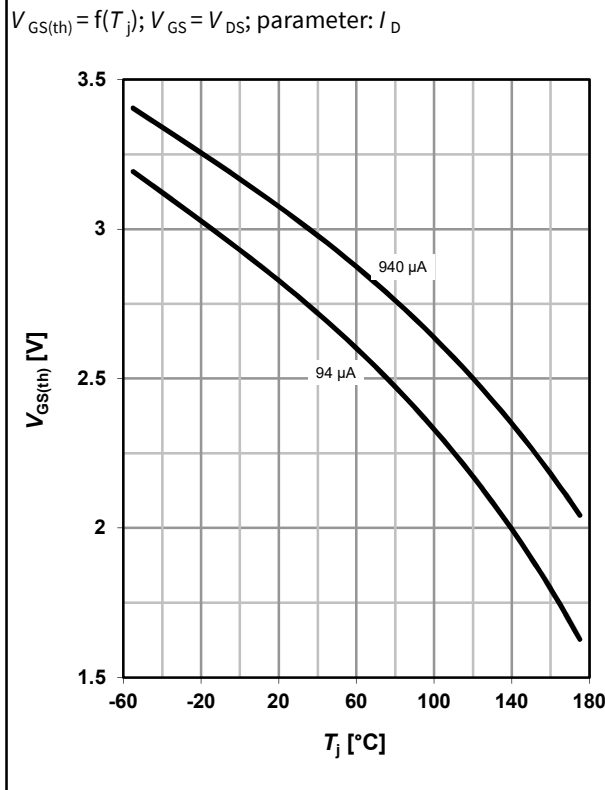


8 Typ. drain-source on-state resistance

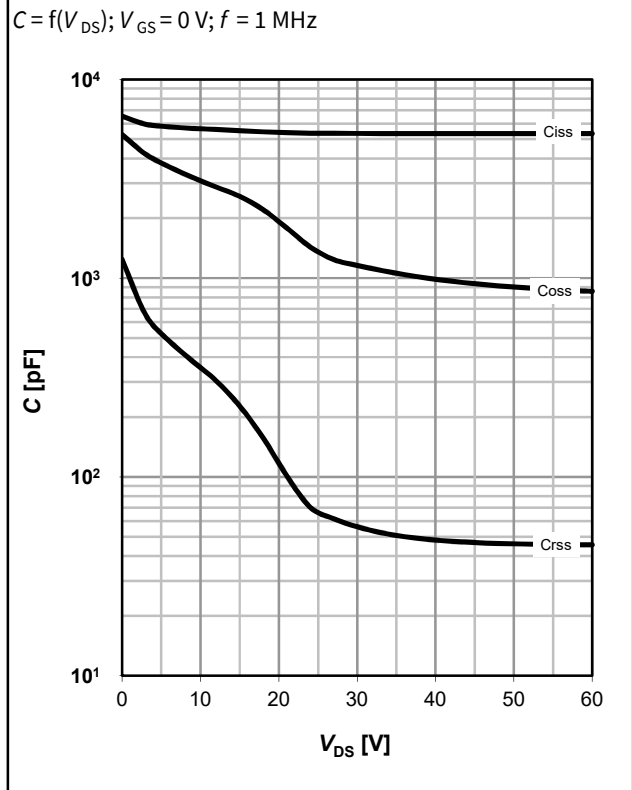
$R_{DS(on)} = f(T_j); \text{parameter: } I_D, V_{GS}$



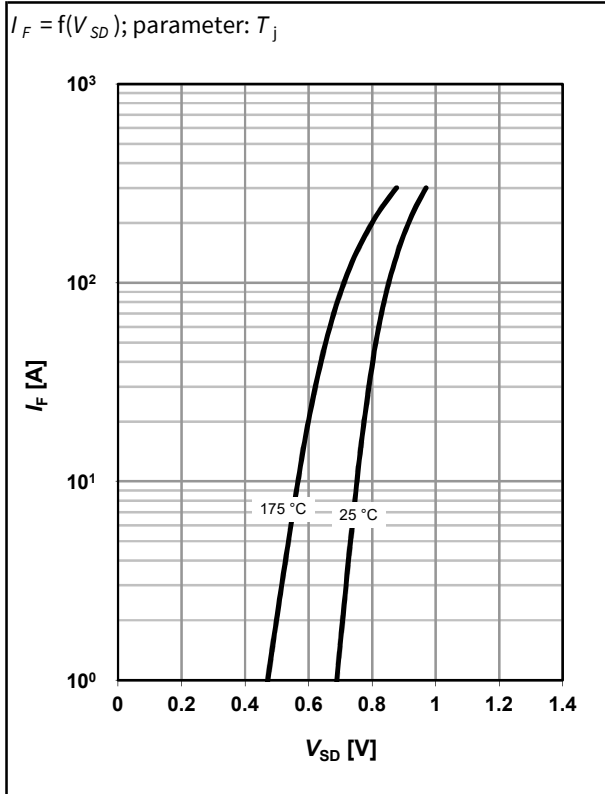
9 Typ. gate threshold voltage



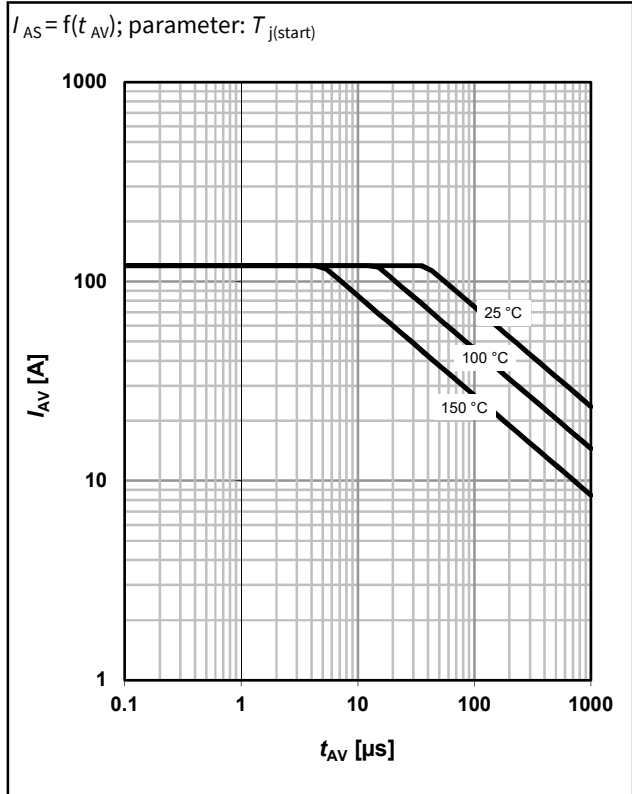
10 Typ. capacitances



11 Typical forward diode characteristics

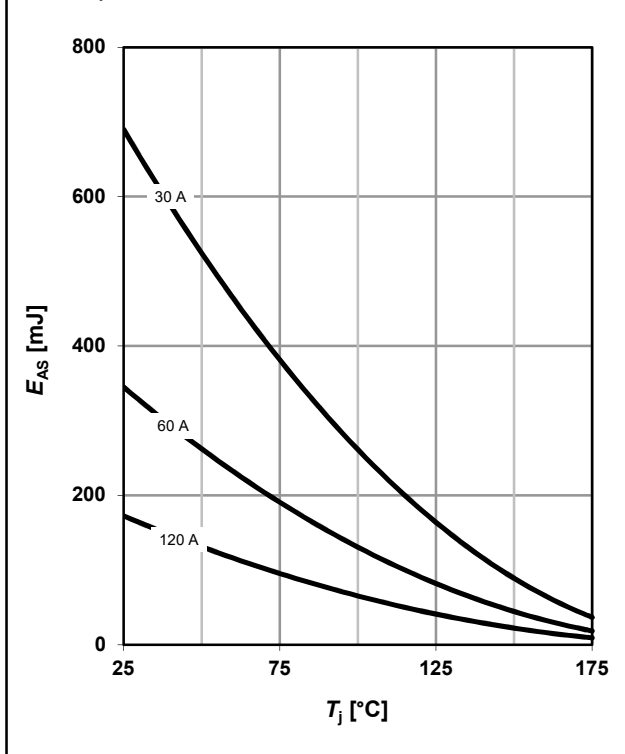


12 Typ. avalanche characteristics



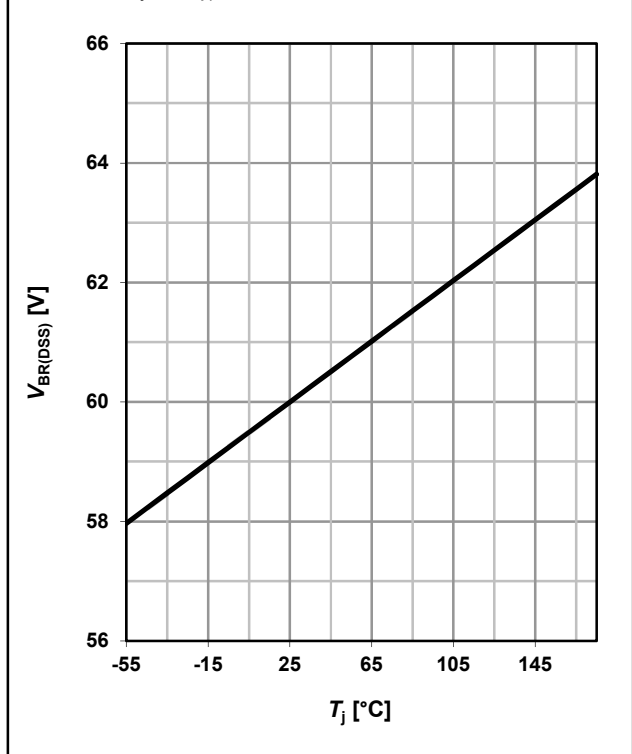
13 Typical avalanche energy

$E_{AS} = f(T_j)$; parameter: I_D



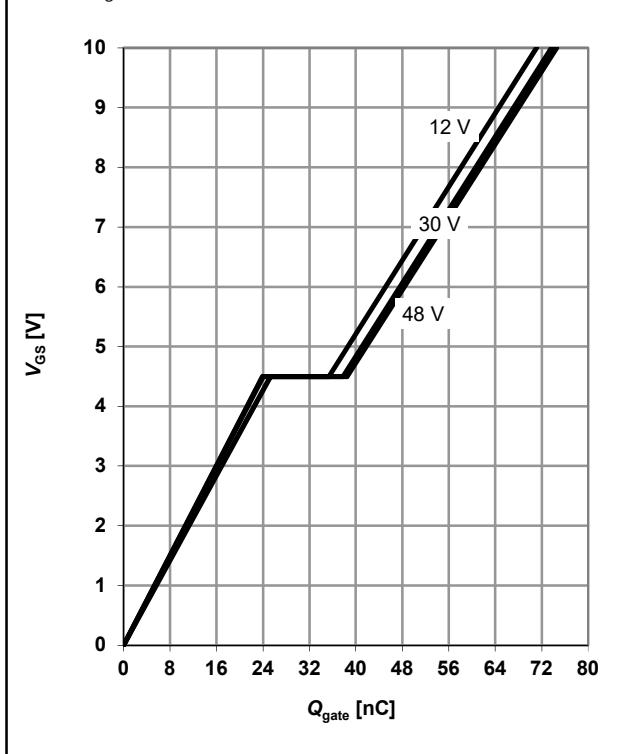
14 Drain-source breakdown voltage

$V_{BR(DSS)} = f(T_j)$; $I_{D_typ} = 1\text{ mA}$

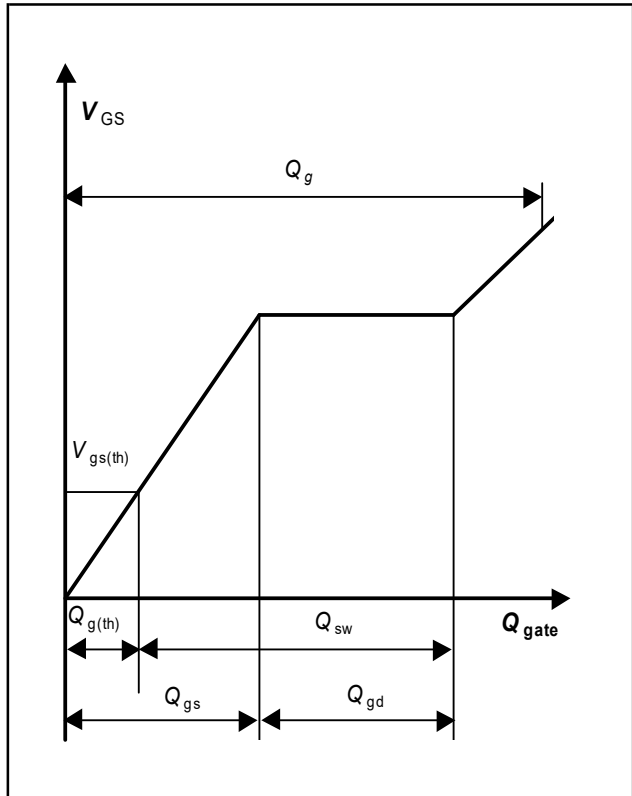


15 Typ. gate charge

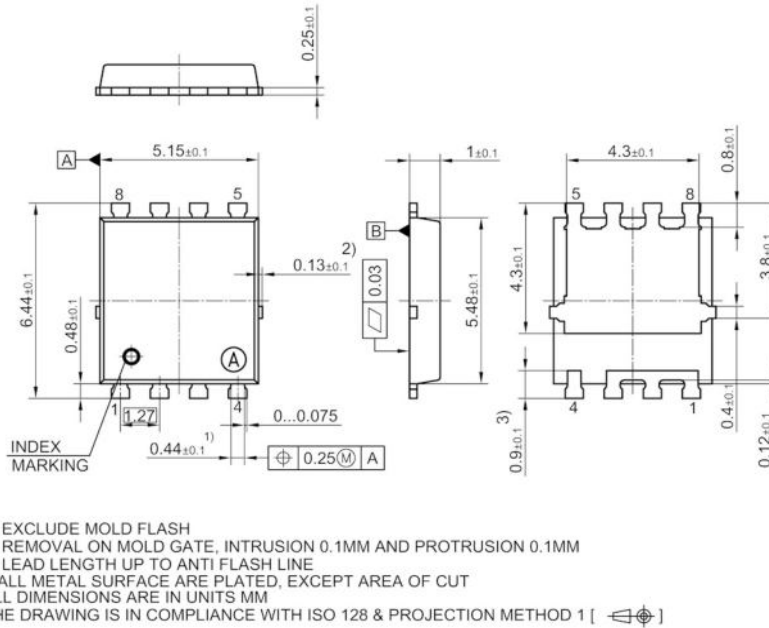
$V_{GS} = f(Q_{gate})$; $I_D = 60\text{ A}$ pulsed; parameter: V_{DD}



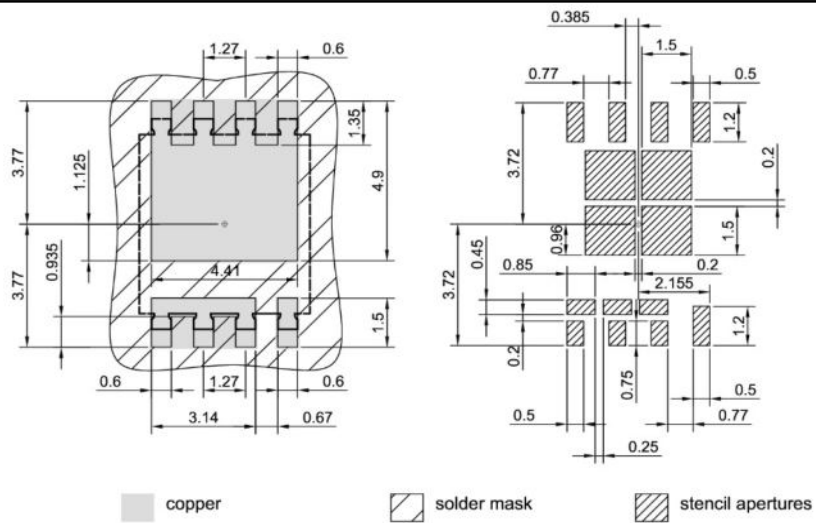
16 Gate charge waveforms



Package Outline

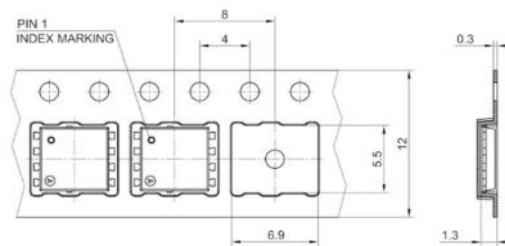


Footprint



All dimensions are in units mm

Packaging



ALL DIMENSIONS ARE IN UNITS MM
 THE DRAWING IS IN COMPLIANCE WITH ISO 128 & PROJECTION METHOD 1 [1]

Revision History

Revision	Date	Changes
Revision 1.0	2024-04-11	Final Data Sheet

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